

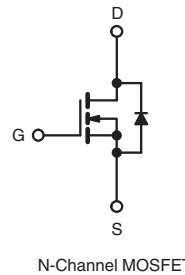
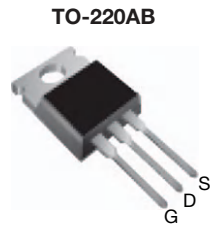
## 2SK2798-VB Datasheet

### N-Channel 500V (D-S)Power MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	500	
R <sub>DS(on)</sub> (Ω)	V <sub>GS</sub> = 10 V	0.660
Q <sub>g</sub> (Max.) (nC)	81	
Q <sub>gs</sub> (nC)	20	
Q <sub>gd</sub> (nC)	36	
Configuration	Single	

#### FEATURES

- Lower Gate Charge Q<sub>g</sub> Results in Simpler Drive Requirements
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage
- Compliant to RoHS Directive 2002/95/EC




ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V <sub>DS</sub>	500	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C	13	
		T <sub>C</sub> = 100 °C	8.1	
Pulsed Drain Current <sup>a</sup>	I <sub>DM</sub>	50	A	
Linear Derating Factor		2.0	W/°C	
Single Pulse Avalanche Energy <sup>b</sup>	E <sub>AS</sub>	560	mJ	
Avalanche Current <sup>a</sup>	I <sub>AR</sub>	13	A	
Repetitive Avalanche Energy <sup>a</sup>	E <sub>AR</sub>	25	mJ	
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	250	W
Peak Diode Recovery dV/dt <sup>c</sup>	dV/dt	9.2	V/ns	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 150	°C	
Soldering Recommendations (Peak Temperature)	for 10 s	300 <sup>d</sup>		
Mounting Torque	6-32 or M3 screw	10		lbf · in
		1.1	N · m	

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting T<sub>J</sub> = 25 °C, L = 5.7 mH, R<sub>g</sub> = 25 Ω, I<sub>AS</sub> = 14 A, dV/dt = 7.6 V/ns (see fig. 12a).
- I<sub>SD</sub> ≤ 14 A, dI/dt ≤ 250 A/μs, V<sub>DD</sub> ≤ V<sub>DS</sub>, T<sub>J</sub> ≤ 150 °C.
- 1.6 mm from case.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Case-to-Sink, Flat, Greasd Surface	$R_{thCS}$	0.50	-	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.50	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$	500	-	-	V	
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$	-	0.55	-	V/°C	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V	
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 500\text{ V}$ , $V_{GS} = 0\text{ V}$	-	-	25	$\mu\text{A}$	
		$V_{DS} = 400\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ }^\circ\text{C}$	-	-	250		
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$   $I_D = 8.4\text{ A}^b$	-	0.660	-	$\Omega$	
Forward Transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}$ , $I_D = 8.4\text{ A}$	8.1	-	-	S	
<b>Dynamic</b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1.0\text{ MHz}$ , see fig. 5	-	1910	-	pF	
Output Capacitance	$C_{oss}$		-	290	-		
Reverse Transfer Capacitance	$C_{rss}$		-	11	-		
Output Capacitance	$C_{oss}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 1.0\text{ V}$ , $f = 1.0\text{ MHz}$	-	2730	-	
			$V_{DS} = 400\text{ V}$ , $f = 1.0\text{ MHz}$	-	82	-	
Effective Output Capacitance	$C_{oss\text{ eff.}}$	$V_{DS} = 0\text{ V to } 400\text{ V}^c$	-	160	-		
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 14\text{ A}$ , $V_{DS} = 400\text{ V}$ , see fig. 6 and 13 <sup>b</sup>	-	-	81	nC
Gate-Source Charge	$Q_{gs}$			-	-	20	
Gate-Drain Charge	$Q_{gd}$			-	-	36	
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10\text{ V}$	$V_{DD} = 250\text{ V}$ , $I_D = 14\text{ A}$ , $R_g = 7.5\text{ }\Omega$ , see fig. 10 <sup>b</sup>	-	15	-	ns
Rise Time	$t_r$			-	39	-	
Turn-Off Delay Time	$t_{d(off)}$			-	39	-	
Fall Time	$t_f$			-	31	-	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	13	A	
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$		-	-	56		
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}$ , $I_S = 14\text{ A}$ , $V_{GS} = 0\text{ V}^b$	-	-	1.5	V	
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}$ , $I_F = 14\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$ , $dI/dt = 100\text{ A}/\mu\text{s}^b$	-	370	550	ns	
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	4.4	6.5	$\mu\text{C}$	
Body Diode Reverse Recovery Current	$I_{RRM}$		-	21	31	A	
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )					

**Notes**

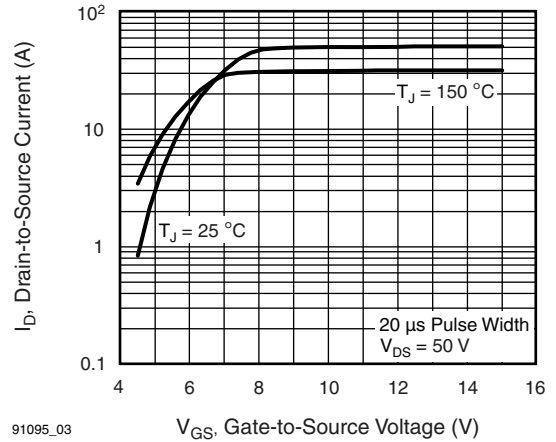
- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- $C_{oss\text{ eff.}}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DS}$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



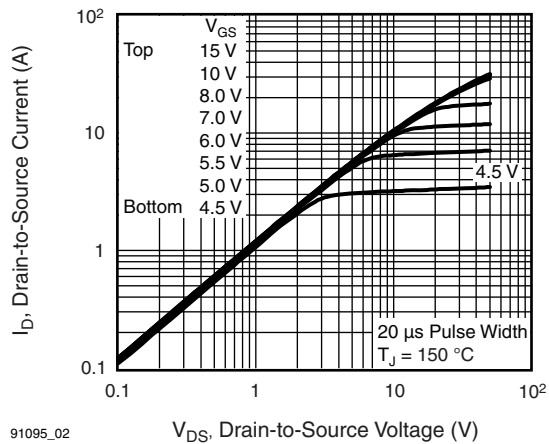
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**Fig. 1 - Typical Output Characteristics**



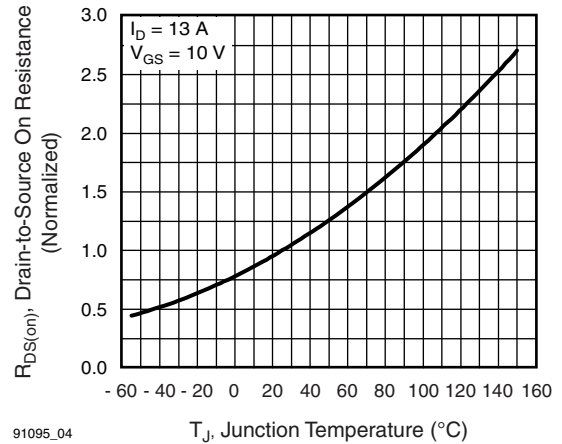
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**Fig. 3 - Typical Transfer Characteristics**



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**Fig. 2 - Typical Output Characteristics**



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**Fig. 4 - Normalized On-Resistance vs. Temperature**



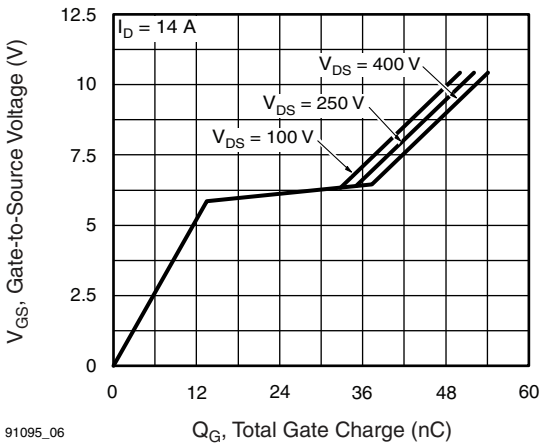
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Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



91095\_07

Fig. 7 - Typical Source-Drain Diode Forward Voltage



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Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



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Fig. 8 - Maximum Safe Operating Area



Fig. 9 - Maximum Drain Current vs. Case Temperature



Fig. 10a - Switching Time Test Circuit



Fig. 10b - Switching Time Waveforms



Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



Fig. 12a - Unclamped Inductive Test Circuit



Fig. 12b - Unclamped Inductive Waveforms



Fig. 12c - Maximum Avalanche Energy vs. Drain Current

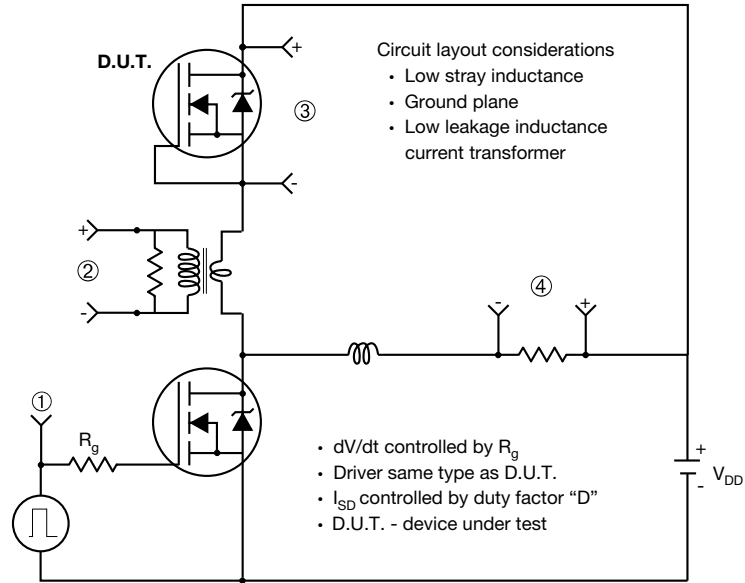


Fig. 13a - Basic Gate Charge Waveform



Fig. 13b - Gate Charge Test Circuit

**Peak Diode Recovery dV/dt Test Circuit**

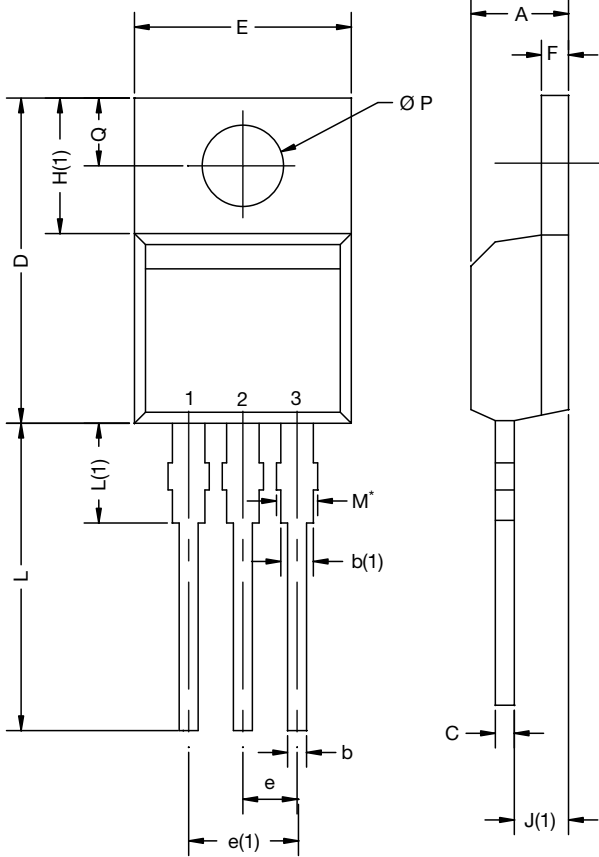


**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

### TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
$\varnothing P$	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: X15-0364-Rev. C, 14-Dec-15  
DWG: 6031

**Note**

- $M^*$  = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM



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